
HN62448I Series

524288-word × 16-bit/1048576-word × 8-bit CMOS Mask
Programmable ROM

HITACHI

ADE-203-772A (Z)
Rev. 1.0
Apr. 24, 1997

Description

The Hitachi HN62448I series is a 8-Mbit CMOS mask-programmable ROM organized either as 524288-word × 16-bit or 1048576-word × 8-bit. It has a high speed normal access time of 100 ns. It is suitable for program and data memory for micro computer systems. It has package variations of standard 42-pin plastic DIP and standard 44-pin plastic SOP.

Features

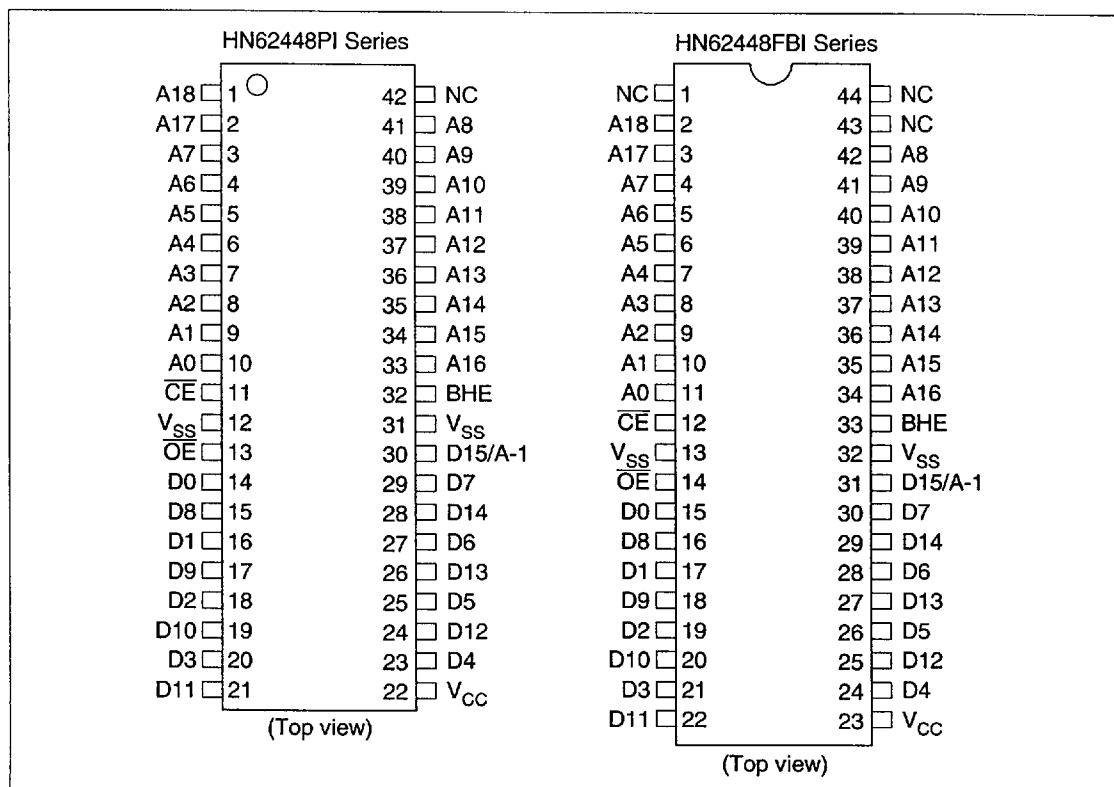
- Single 5 V supply : 5.0 V ± 10%
- Access time:
 - Normal access time: 100 ns (max)
- Power dissipation
 - Active: 550 mW (max)
 - Standby: 165 μW (max)
- Byte-wide or word-wide data organization with byte/word selection (BHE)
- Three-state data output for wired or-tying
- Directly TTL compatible all inputs and outputs
- Operating temperature rage: -40 to +85°C

Ordering Information

Type No.	Access time	Package
HN62448PI-10	100 ns	600mil 42-pin plastic DIP (DP-42)
HN62448FBI-10	100 ns	600mil 44-pin plastic SOP (FP-44D)

HN62448I Series

Pin Arrangement



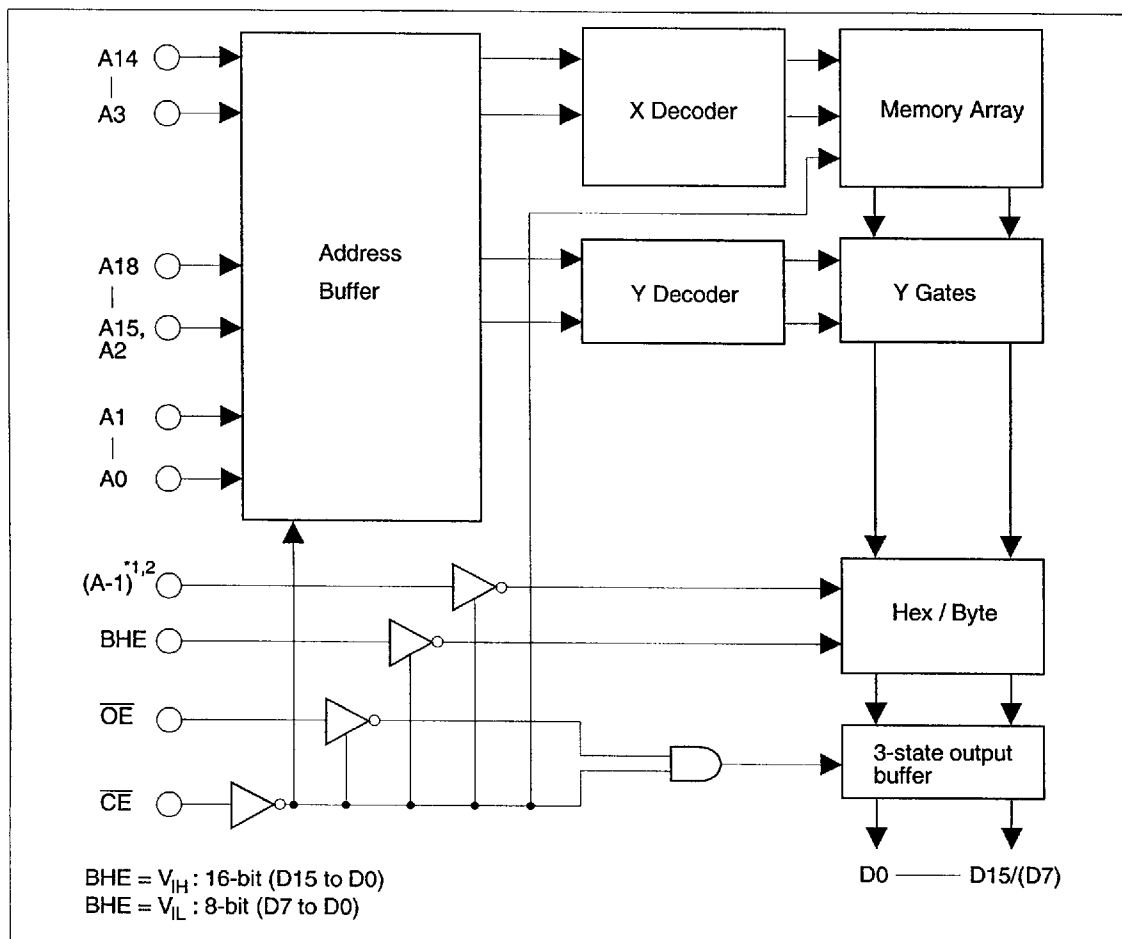
Pin Description

Pin name	Function
A-1, A0 to A18	Address input
D0 to D15	Data output
$\overline{OE}$	Output enable
$\overline{CE}$	Chip enable
BHE	Byte/word selection
V_{CC}	Power supply
V_{SS}	Ground
NC	No connection

Block Diagram

Notes: 1. A-1 is least significant address.

2. When BHE is 'low', D14 to D8 goes the high impedance state, and D15 should be A-1.



HN62448I Series

Mode Selection

Mode	Pin				Data output		Address input	
	$\overline{CE}$	$\overline{OE}$	BHE	D15/A-1	D0-D7	D8-D15	LSB	MSB
Standby	H	x*1	x	x	High-Z	High-Z	—	—
Output disable	L	H	x	x	High-Z	High-Z	—	—
Read (16-bit)	L	L	H	Dout	D0 to D7	D8 to D15	A0	A18
Read (8-bit)	L	L	L	L	D0 to D7	High-Z	A-1	A18
Read (8-bit)	L	L	L	H	D8 to D15	High-Z	A-1	A18

Note: 1. x: Don't care.

Absolute Maximum Ratings

Parameter	Symbol	Value	Unit
Power supply voltage relative to V_{SS}	V_{CC}	-0.3 to +7.0	V
All input and output voltage relative to V_{SS}	V_{in}, V_{out}	-0.3 to $V_{CC} + 0.3$	V
Operating temperature range	T_{opr}	-40 to 85	°C
Storage temperature range	T_{stg}	-55 to +125	°C
Storage temperature range under bias	T_{bias}	-40 to +85	°C

DC Operating Conditions ($T_a = -40$ to $+85^\circ\text{C}$)

Parameter	Symbol	Min	Typ	Max	Unit
Supply voltage	V_{CC}	4.5	5.0	5.5	V
	V_{SS}	0	0	0	V
Input high voltage	V_{IH}	2.2	—	$V_{CC} + 0.3$	V
Input low voltage	V_{IL}	-0.3	—	0.8	V

DC Characteristics ($V_{CC} = 5.0 \text{ V} \pm 10\%$, $V_{SS} = 0 \text{ V}$, $T_a = -40 \text{ to } +85^\circ\text{C}$)

Parameter	Symbol	Min	Max	Unit	Test conditions
Operating V_{CC} current	I_{CC}	—	100	mA	$V_{CC} = 5.5 \text{ V}$, $I_{DOUT} = 0 \text{ mA}$, $t_{RC} = 100 \text{ ns}$
Standby V_{CC} current	I_{SB1}	—	30	μA	$V_{CC} = 5.5 \text{ V}$, $\overline{CE} \geq V_{CC} - 0.2 \text{ V}$
	I_{SB2}	—	3	mA	$V_{CC} = 5.5 \text{ V}$, $\overline{CE} = 2.2 \text{ V}$
Input leakage current	$ I_{IL} $	—	10	μA	$V_{in} = 0 \text{ to } V_{CC}$
Output leakage current	$ I_{OL} $	—	10	μA	$\overline{CE} = 2.2 \text{ V}$, $V_{OUT} = 0 \text{ to } V_{CC}$
Output high voltage	V_{OH}	2.4	—	V	$I_{OH} = -205 \mu\text{A}$
Output low voltage	V_{OL}	—	0.4	V	$I_{OL} = 1.6 \text{ mA}$

Capacitance ($V_{CC} = 5.0 \text{ V} \pm 10\%$, $V_{SS} = 0 \text{ V}$, $T_a = 25^\circ\text{C}$, $V_{in} = 0 \text{ V}$, $f = 1 \text{ MHz}$)

Parameter	Symbol	Min	Max	Unit
Input capacitance	C_{in}	—	10	pF
Output capacitance	C_{out}	—	15	pF

HN62448I Series

AC Characteristics ($V_{CC} = 5.0 \text{ V} \pm 10\%$, $V_{SS} = 0 \text{ V}$, $T_a = -40 \text{ to } +85^\circ\text{C}$)

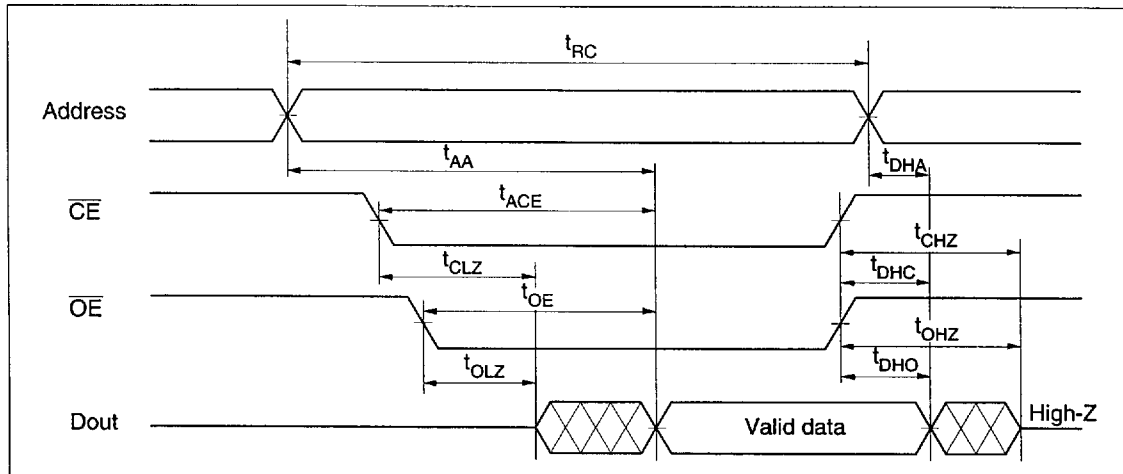
- Input pulse levels: 0.4 to 2.8 V
- Input rise and fall time: 5 ns
- Input and output timing reference levels: 1.5 V
- Output load: 1TTL + $C_L = 100 \text{ pF}$ (including jig)

Parameter	Symbol	HN62448I-10		Unit	Notes
		Min	Max		
Read cycle time	t_{RC}	100	—	ns	
Address access time	t_{AA}	—	100	ns	3
$\overline{CE}$ access time	t_{ACE}	—	100	ns	3
$\overline{OE}$ access time	t_{OE}	—	40	ns	3
BHE access time	t_{BHE}	—	100	ns	
Output hold time from address change	t_{DHA}	0	—	ns	2
Output hold time from $\overline{CE}$	t_{DHC}	0	—	ns	2
Output hold time from $\overline{OE}$	t_{DHO}	0	—	ns	2
Output hold time from BHE	t_{DHB}	0	—	ns	
$\overline{CE}$ to output in high-Z	t_{CHZ}^{*1}	—	40	ns	1
$\overline{OE}$ to output in high-Z	t_{OHZ}^{*1}	—	40	ns	1
BHE to output in high-Z	t_{BHZ}^{*1}	—	40	ns	1
$\overline{CE}$ to output in low-Z	t_{CLZ}	5	—	ns	4
$\overline{OE}$ to output in low-Z	t_{OLZ}	5	—	ns	4
BHE to output in low-Z	t_{BLZ}	5	—	ns	

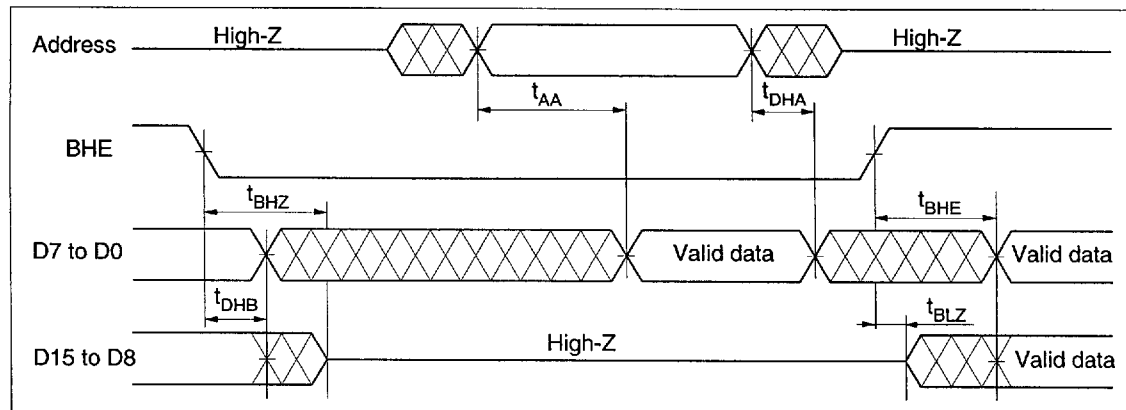
- Notes: 1. t_{CHZ} , t_{OHZ} and t_{BHZ} are defined as the time at which the output achieves the open circuit conditions and are not referred to output voltage levels.
2. t_{DHA} , t_{DHC} , t_{DHO} : Determined by faster.
3. t_{AA} , t_{ACE} , t_{OE} : Determined by slower.
4. t_{CLZ} , t_{OLZ} : Determined by slower.
5. $\overline{CE}$ and $\overline{OE}$ are enable A18 to A0 are valid.
6. D15/A-1 pin is in the output state when BHE is high, $\overline{CE}$ and $\overline{OE}$ are enable. Therefore, the input signals of opposite phase to the output must be applied to them.
7. This device is used ATD (Address Transient Detector). Therefore, transfer either $\overline{CE}$ or address (A2 to A18) after power up to 4.5 V.

Timing Waveforms

Word Mode (BHE = 'V_{IH}') or Byte Mode (BHE = 'V_{IL}')*2, 3, 4



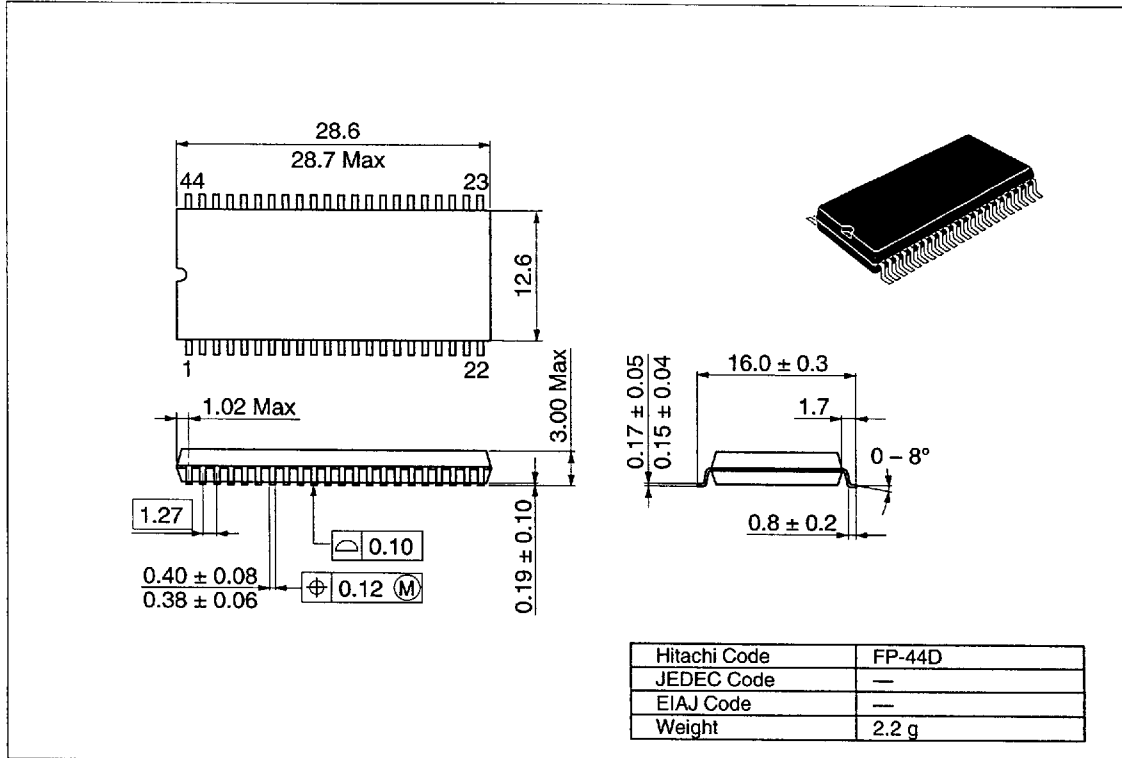
Word Mode, Byte Mode Switch*5, 6



HN62448I Series

HN62448FBI Series (FP-44D)

Unit: mm



HITACHI

HN62448I Series

Disclaimer

When using this document, keep the following in mind:

1. This document may, wholly or partially, be subject to change without notice.
2. All rights are reserved: No one is permitted to reproduce or duplicate, in any form, the whole or part of this document without Hitachi's permission.
3. Hitachi will not be held responsible for any damage to the user that may result from accidents or any other reasons during operation of the user's unit according to this document.
4. Circuitry and other examples described herein are meant merely to indicate the characteristics and performance of Hitachi's semiconductor products. Hitachi assumes no responsibility for any intellectual property claims or other problems that may result from applications based on the examples described herein.
5. No license is granted by implication or otherwise under any patents or other rights of any third party or Hitachi, Ltd.
6. **MEDICAL APPLICATIONS:** Hitachi's products are not authorized for use in **MEDICAL APPLICATIONS** without the written consent of the appropriate officer of Hitachi's sales company. Such use includes, but is not limited to, use in life support systems. Buyers of Hitachi's products are requested to notify the relevant Hitachi sales offices when planning to use the products in **MEDICAL APPLICATIONS**.

Sales Offices

HITACHI

Hitachi, Ltd.

Semiconductor & IC Div.
Nippon Bldg., 2-6-2, Ohte-machi, Chiyoda-ku, Tokyo 100, Japan
Tel: Tokyo (03) 3270-2111
Fax: (03) 3270-5109

For further information write to:

Hitachi America, Ltd.
Semiconductor & IC Div.
2000 Sierra Point Parkway
Brisbane, CA. 94005-1835
U S A
Tel: 415-589-8300
Fax: 415-583-4207

Hitachi Europe GmbH
Electronic Components Group
Continental Europe
Domacher Straße 3
D-85622 Feldkirchen
München
Tel: 089-9 91 80-0
Fax: 089-9 29 30 00

Hitachi Europe Ltd.
Electronic Components Div.
Northern Europe Headquarters
Whitebrook Park
Lower Cookham Road
Maidenhead
Berkshire SL6 8YA
United Kingdom
Tel: 0628-585000
Fax: 0628-778322

Hitachi Asia Pte. Ltd.
16 Collyer Quay #20-00
Hitachi Tower
Singapore 0104
Tel: 535-2100
Fax: 535-1533

Hitachi Asia (Hong Kong) Ltd.
Unit 706, North Tower,
World Finance Centre,
Harbour City, Canton Road
Tsim Sha Tsui, Kowloon
Hong Kong
Tel: 27359218
Fax: 27306071

Revision Record

Rev.	Date	Contents of Modification	Drawn by	Approved by
1.0	Apr. 24, 1997	Initial issue		
